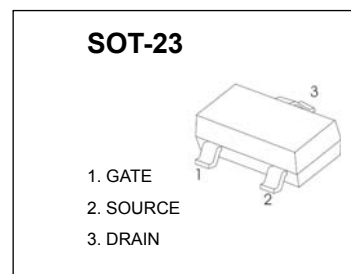




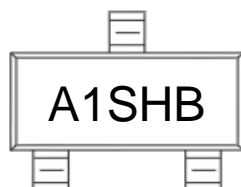
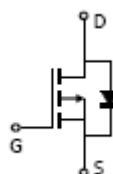
$V_{(BR)DSS}$	$R_{DS(on)MAX}$	$I_D$
-19V	100 mΩ@-4.5V	2.5A
	130 mΩ@-2.5V	

**FEATURE**

TrenchFET Power MOSFET

**APPLICATION**

- Load Switch for Portable Devices
- DC/DC Converter

**MARKING****Equivalent Circuit****Maximum ratings ( $T_a=25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	-19	V
Gate-Source Voltage	$V_{GS}$	$\pm 10$	
Continuous Drain Current ( $T_J=150^\circ\text{C}$ )	$I_D$	-2.5	A
Pulsed Drain Current	$I_{DM}$	-10	
Continuous Source-Drain Diode Current	$I_S$	-0.72	
Maximum Power Dissipation	$P_D$	0.35	W
Thermal Resistance from Junction to Ambient( $t \leq 5s$ )	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 ~ +150	

**MOSFET ELECTRICAL CHARACTERISTICS****T<sub>a</sub> = 25 °C unless otherwise specified**

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Static</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA		-19.5		V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-0.5		-0.9	
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±8V			±100	nA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V			-1	μA
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -1.5A		0.085	0.100	Ω
		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -1.5A		0.105	0.130	
Forward transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = -5V, I <sub>D</sub> = -2.8A		4.0		S
<b>Dynamic<sup>b</sup></b>						
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V, f = 1MHz		405		pF
Output capacitance	C <sub>oss</sub>			75		
Reverse transfer capacitance	C <sub>rss</sub>			55		
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> = -10V, V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3A		5.5	10	nC
Gate-source charge	Q <sub>gs</sub>	V <sub>DS</sub> = -10V, V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -3A		3.3	6	
Gate-drain charge	Q <sub>gd</sub>			0.7		
Gate resistance	R <sub>g</sub>	f = 1MHz		6.0		Ω
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = -10V, R <sub>L</sub> = 10Ω, I <sub>D</sub> = -1A, V <sub>GEN</sub> = -4.5V, R <sub>g</sub> = 1Ω		11	20	ns
Rise time	t <sub>r</sub>			35	60	
Turn-off delay time	t <sub>d(off)</sub>			30	50	
Fall time	t <sub>f</sub>			10	20	
<b>Drain-source body diode characteristics</b>						
Continuous source-drain diode current	I <sub>S</sub>	T <sub>C</sub> = 25°C			-1.3	A
Pulse diode forward current <sup>a</sup>	I <sub>SM</sub>				-10	
Body diode voltage	V <sub>SD</sub>	I <sub>S</sub> = -0.7A		-0.8	-1.2	V

**Notes :**

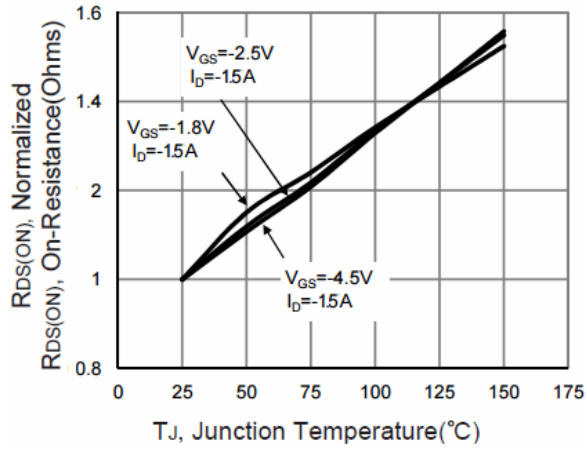
a. Pulse Test : Pulse Width &lt; 300μs, Duty Cycle ≤ 2%.

b. Guaranteed by design, not subject to production testing.

**IV. Temperature Vs R<sub>DS(ON)</sub> / V<sub>GS(th)</sub>**



$R_{DS(ON)}$  vs Junction Temperature



$V_{GS(th)}$  vs Junction Temperature

